EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	50	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((bit or bitline or bit-line or (bit near line)) near10 (etch or etching or etched))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:07
L2	2	(contactless near (flash or nonvolatile or non-volatile) near memory) and (one near dimensional near (slot or line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:08
L3	2	(contactless near (flash or nonvolatile or non-volatile) near memory) and (one near (dimension or dimensional) near (slot or line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:08
L4	2	(contactless near (flash or nonvolatile or non-volatile) near memory) and (one near2 (dimension or dimensional) near2 (slot or line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:08
L5	2	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((single or one) near2 (dimension or dimensional) near2 (slot or line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:08
L6	133	(contactless near (flash or nonvolatile or non-volatile) near memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:48
L7	84	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((bit or bitline or bit-line or (bit near line)) near5 (form or forming or formed or formation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:49
L8	77	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((bit or bitline or bit-line or (bit near line)) near2 (form or forming or formed or formation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:53

L9	46	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((bit or bitline or bit-line or (bit near line)) near2 (form or forming or formed or formation)) and ((slot or line) near10 (width or length or dimension))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:54
L10	43	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((bit or bitline or bit-line or (bit near line)) near2 (form or forming or formed or formation)) and ((slot or line) near5 (width or length or dimension))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:55
L11	12	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((bit or bitline or bit-line or (bit near line)) near2 (form or forming or formed or formation)) and ((slot or line) near5 (width or length or dimension) near5 (bit or bitline or bit-line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:56
L12	1	(contactless near (flash or nonvolatile or non-volatile) near memory) and ((bit or bitline or bit-line or (bit near line)) near2 (form or forming or formed or formation)) and ((slot or line) near5 (width or length or dimension) near5 (bit or bitline or bit-line)) and resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:56
L13	1044	((slot or line) near5 (width or length or dimension) near5 (bit or bitline or bit-line)) and resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:56
L14	940	((slot or line) near5 (width or length or dimension) near5 (bit or bitline or bit-line)) and resist and (pattern or patterning or patterned)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:57
L15	1546	((slot or line) near5 (width or length or dimension) near5 (bit or bitline or bit-line)) and (photoresist or photo-resist or resist) and (pattern or patterning or patterned)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:57

EAST Search History

L16	14	((slot) near5 (width or length or dimension) near5 (bit or bitline or bit-line)) and (photoresist or photo-resist or resist) and (pattern or patterning or patterned)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:58
L17	2	((slot) near5 (width or length or dimension) near5 (bit or bitline or bit-line)) and (photoresist or photo-resist or resist) and (pattern or patterning or patterned) and (wordline or word-line or (word near line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:58
L18	317	slot and (photoresist or photo-resist or resist) and (pattern or patterning or patterned) and (wordline or word-line or (word near line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 11:59
L19	13	slot and (photoresist or photo-resist or resist) and (pattern or patterning or patterned) and (wordline or word-line or (word near line)) and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:00
L20	13	slot and (photoresist or photo-resist or resist) and (pattern or patterning or patterned) and (wordline or word-line or (word near line)) and contactless and (etch or etching or etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:01
L21	209	(line or opening or slot) same (etch or etching or etched) same (bl or bitline or bit-line or (bit near line)) and (photoresist or photo-resist or resist) and (pattern or patterning or patterned) and (wordline or word-line or (word near line)) and contactless and (etch or etching or etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:02
L22	209	((line or opening or slot) same (etch or etching or etched) same (bl or bitline or bit-line or (bit near line))) and (photoresist or photo-resist or resist) and (pattern or patterning or patterned) and (wordline or word-line or (word near line)) and contactless and (etch or etching or etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:03

EAST Search History

L23	44	(contactless same (line or opening or slot) same (etch or etching or etched) same (bl or bitline or bit-line or (bit near line))) and (photoresist or photo-resist or resist) and (pattern or patterning or patterned) and (wordline or word-line or (word near line)) and contactless and (etch or etching or etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:03
L24	21	(contactless same (line or opening or slot) same (etch or etching or etched) same (bl or bitline or bit-line or (bit near line))) same (pattern or patterning or patterned) same (resist or photoresist or photo-resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:05
L25	0	(contactless same (line or opening or slot) same (etch or etching or etched) same (bl or bitline or bit-line or (bit near line))) same (pattern or patterning or patterned) same (resist or photoresist or photo-resist) and ild	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:05
L26	3	(contactless same (line or opening or slot) same (etch or etching or etched) same (bl or bitline or bit-line or (bit near line))) same (pattern or patterning or patterned) same (resist or photoresist or photo-resist) and interlayer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:05
L29	41	(contactless near2 memory) and (lithography or photolithography) and (etch or etching or etched) and ((dimensional or dimension or length or width or height) near5 (opening or slot or hole or line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:08
L30	17	(contactless near2 memory) and (lithography or photolithography) and (etch or etching or etched) and ((dimensional or dimension or length or width or height) near5 (opening or slot or hole or line)) with bit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:08

EAST Search History

L31	15	(contactless near2 memory) and (lithography or photolithography) and (etch or etching or etched) and ((dimensional or dimension or length or width or height) near5 (opening or slot or hole or line)) with bit and (resist or photoresist or photo-resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:09
L32	0	(contactless near2 memory) and (lithography or photolithography) and (etch or etching or etched) same ((dimensional or dimension or length or width or height) near5 (opening or slot or hole or line)) same bit same (resist or photoresist or photo-resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:09
L33	0	(contactless near2 memory) and (lithography or photolithography) same (etch or etching or etched) same ((dimensional or dimension or length or width or height) near5 (opening or slot or hole or line)) same bit same (resist or photoresist or photo-resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:10
L34	3	(contactless near2 memory) and (lithography or photolithography) same (etch or etching or etched) same ((opening or slot or hole or line)) same bit same (resist or photoresist or photo-resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 12:10
L35	62	(contactless near2 memory) and (gate near stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:14
L36	58	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:18
L37	3	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line)) and slot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:19
L38	30	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line)) and ((slot or opening or line) near5 (pattern or patterning or patterned))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:20

L39	3	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line)) and ((slot or opening or line) near5 (pattern or patterning or patterned) near5 width)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:21
L40	16	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line)) and ((slot or opening or line) near5 width)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:21
L41	0	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line)) and ((slot or opening or line) near5 width) and ((slot or opening or line) near5 lenght)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:21
L42	4	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line)) and ((slot or opening or line) near5 width) and ((slot or opening or line) near5 length)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:22
L43	4	(contactless near2 memory) and (gate near stack) and (bl or bit-line or bitline or (bit near line)) and ((slot or opening or line) near5 (wide or width)) and ((slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:23
L44	38	(contactless near2 memory) and ((slot or opening or line) near5 (wide or width)) and ((slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:23
L45	6	(contactless near2 memory) same ((slot or opening or line) near5 (wide or width)) and ((slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:23
L46	5	(contactless near2 memory) same ((slot or opening or line) near5 (wide or width)) same ((slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:24
L47	24	(contactless near2 memory) and ((slot or opening or line) near5 (wide or width)) same ((slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:24

L48	24	(contactless near2 memory) and ((slot or opening or line) near5 (wide or width)) near10 ((slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:27
L49	25	(contactless near2 memory) and ((column or slot or opening or line) near5 (wide or width)) near10 ((column or slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:32
L50	25	(contactless near2 memory) and ((column or slot or opening or line or bitline or gateline) near5 (wide or width)) near10 ((column or slot or opening or line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:33
L51	25	(contactless near2 memory) and ((column or slot or opening or line or bitline or gateline or bit-line) near5 (wide or width)) near10 ((column or slot or opening or line or bitline or gateline or bit-line) near5 (long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:33
L52	28	(contactless near2 memory) and ((column or slot or opening or line or bitline or gateline or bit-line) near5 (wide or width)) near10 ((column or slot or opening or line or bitline or gateline or bit-line) near5 (dimension or long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:34
L53	26	(contactless near2 memory) and ((column or slot or opening or line or bitline or gateline or bit-line) near5 (wide or width or dimension)) near10 ((column or slot or opening or line or bitline or gateline or bit-line) near5 (dimension or long or longer or length))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:35
L54	1	(contactless near2 memory) and ((bitline or bit-line or bit or line or opening or column or slot) near2 (dimension or dimensional)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:36
L55	3	(contactless near2 memory) and ((bitline or bit-line or bit or line or opening or column or slot) near5 (dimension or dimensional)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:36

L56	20	(contactless near2 memory) and ((bitline or bit-line or bit or line or opening or column or slot) near5 (width or length or dimension or dimensional)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:38
L57	0	(contactless near2 memory) and (lenght near2 slot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:38
L58	2	(contactless near2 memory) and (length near2 slot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:38
L59	1	(contactless near2 memory) and (length near2 slot) and (width near2 slot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:38
L60	1	(contactless near2 memory) and (length near2 (line or column or slot)) and (width near2 slot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:39
L61	7	(contactless near2 memory) and (length near2 (line or column or slot)) and (width near2 (line or column or slot))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:39
L62	14	(contactless near5 memory) and (length near2 (line or column or slot)) and (width near2 (line or column or slot))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:40
L63	2	(contactless near5 memory) and (length near2 (line or column or slot)) near10 (width near2 (line or column or slot))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:41
L64	6	(contactless near5 memory) and ((slot or line) near2 dimension)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:43
L65	106	(contactless near5 memory) and (length near5 width)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:48

EAST Search History

L66	25	(contactless near5 memory) and (length near5 width) and (nor near2 (memory or cell or array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:51
L67	19	"5734607"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:51

| L83 | 317 | (US-20050196918-$ or US-20050139882-$ or US-20020115255-$ or US-20040255259-$ or US-20040000687-$ or US-20040227167-$ or US-20050121755-$ or US-20030127683-$ or US-20020190312-$ or US-20010050439-$ or US-20040253791-$ or US-20040033664-$ or US-20050009332-$ or US-20030032219-$ or US-20020068429-$ or US-20020149050-$ or US-20020088996-$ or US-20030119272-$ or US-20040056324-$ or US-20040266126-$ or US-20040000717-$ or US-20050139935-$ or US-20040084713-$ or US-20030075734-$ or US-20040021164-$ or US-20020038911-$).did. or (US-20050082593-$ or US-20020080317-$ or US-20040217406-$ or US-20020047121-$ or US-20020187598-$ or US-20030127677-$ or US-20050106761-$ or US-20050068834-$ or US-20040175924-$ or US-20020119618-$ or US-20020119623-$ or US-20020135072-$ or US-20020146899-$ or US-20060139992-$ or US-20040084719-$ or US-20010017800-$ or US-20020175381-$ or US-20020081806-$ or US-20030124845-$ or US-20050140002-$ or US-20040224262-$ or US-20050225740-$ or US-20060267224-$ or US-20070023806-$ or US-20040038478-$ or US-20060193191-$ or US-20060183284-$).did. or (US-20060018164-$ or US-20060013599-$ or US-20050179079-$ or US-20050116279-$ or US-20050106812-$ or | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/05/03 13:54 |

EAST Search History

L84	77	I83 and (nor near2 (cell or array or memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:55
L85	62	I83 and (nor near2 (cell or array or memory)) and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:55
L86	55	I83 and (nor near2 (cell or array or memory)) and contactless and width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:55
L87	43	I83 and (nor near2 (cell or array or memory)) and contactless and width and length	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:56
L88	23	I83 and (nor near2 (cell or array or memory)) and contactless and width and length and (lithography or photolithography) and (resist or photoresist or photo-resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:57
L89	23	I83 and (nor near2 (cell or array or memory)) and contactless and width and length and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:57
L90	3	I83 and (nor near2 (cell or array or memory)) and contactless and width and length and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and (gate adj stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:59
L91	3	I83 and (nor near2 (cell or array or memory)) and contactless and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and (gate adj stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 13:59

L92	6	(nor near2 (cell or array or memory)) and contactless and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and (gate adj stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:00
L93	4	(nor near2 (cell or array or memory)) and contactless and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and (gate adj stack) and slot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:01
L94	4	(nor near2 (cell or array or memory)) and contactless and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and slot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:01
L95	1	(contactless near2 memory) and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and slot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:01
L96	5	(contactless near5 memory) and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and slot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:02
L97	105	(contactless near5 memory) and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and (slot or line or column) near5 (etch or etching or etched or form or forming or formed or formation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:03
L98	35	(contactless near5 memory) and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and (slot or line or column or opening) near10 (etch or etching or etched or form or forming or formed or formation) near10 insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:05

EAST Search History

L99	35	(contactless near5 memory) and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and ((slot or line or column or opening) near10 (etch or etching or etched or form or forming or formed or formation) near10 insulating)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:05
L100	9	(contactless near5 memory) and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and ((slot or line or column or opening) near10 (etch or etching or etched or form or forming or formed or formation) near10 insulating) and ((column or opening or slot) near5 (width or length or dimension))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:06
L101	9	(contactless near5 memory) and (lithography or photolithography) and (resist or photoresist or photo-resist) and (pattern or patterning or patterned) and ((slot or line or column or opening) near10 (etch or etching or etched or form or forming or formed or formation) near10 insulating) and ((column or opening or slot) near5 (width or length or dimension or dimensional))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:10
L102	0	(contactless near2 memory) and (slot near2 lenght)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:10
L103	2	(contactless near2 memory) and (slot near2 length)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:10
L104	2	(contactless near2 memory) and (slot near5 length)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:11

L105	5	(contactless near2 memory) and (slot near5 (width or length or dimension or distance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:34
L106	135	(contactless near2 memory) and ((line or opening or slot) near5 (width or length or dimension or distance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:34
L107	19	(contactless near2 memory) and ((line or opening or slot) near5 (width or length or dimension or distance)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:34
L108	1	(contactless near2 memory).clm. and ((line or opening or slot) near5 (width or length or dimension or distance)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:34
L109	18	(contactless near2 memory) and ((line or opening or slot) near5 (width or length or dimension or distance)).clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:46
L110	19	(contactless near2 memory) and ((column or line or opening or slot) near5 (width or length or dimension or distance)).clm. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:47
L111	970	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:49
L112	226	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:49

EAST Search History

L113	52	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:49
L114	52	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory) and (etch or etching or etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:50
L115	4	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory) and (etch or etching or etched) and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:51
L116	8	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory) and (etch or etching or etched) and slot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:51

L117	43	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory) and (etch or etching or etched) and (bit or bitline or bit-line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:51
L118	43	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory) and (etch or etching or etched) and (bl or bit or bitline or bit-line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:52
L119	14	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory) and (etch or etching or etched) and (bl or bit or bitline or bit-line).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:58
L120	4	(gate adj stack) and ((active or semiconductor) near (region or area or layer)) and (pattern or patterning or patterned) and (resist or photoresist or photo-resist) and (lithography or photolithography or photo-lithography) and plug and ((nonvolatile or non-volatile or flash) near2 memory) and (etch or etching or etched) and (bl or bit or bitline or bit-line) and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 14:59

EAST Search History

L121	49	(contactless near2 (bl or (bit near line) or bitline or bit-line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:00
L122	46	(contactless near2 (bl or (bit near line) or bitline or bit-line)) and (pattern or patterning or patterned)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:01
L123	12	(contactless near2 (bl or (bit near line) or bitline or bit-line)) and (pattern or patterning or patterned) and (lithography or photolithography or photo-lithography)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:02
L124	7	(contactless near2 (bl or (bit near line) or bitline or bit-line)) and (pattern or patterning or patterned) and (lithography or photolithography or photo-lithography) and (nonvolatile or non-volatile or flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:03
L125	1	(contactless near2 (bl or (bit near line) or bitline or bit-line)) and (pattern or patterning or patterned) and (lithography or photolithography or photo-lithography) and (nonvolatile or non-volatile or flash) and (nor near2 flash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:03
L126	1	(contactless near2 (bl or (bit near line) or bitline or bit-line)) and (pattern or patterning or patterned) and (lithography or photolithography or photo-lithography) and (nonvolatile or non-volatile or flash) and (nor near2 (memory or cell or flash))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:03
L127	6733	(gate adj stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:04
L128	4412	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:04

EAST Search History

L129	1238	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area)) and (bl or bitline or bit-line or (bit near line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:05
L130	139	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area)) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:05
L131	118	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area)) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:05
L132	98	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area)) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:06
L133	22	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area)) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:06
L134	20	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area)) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and plug and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:08
L135	4	(gate adj stack) and ((active or semiconductor) near2 (layer or region or area)) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and plug and silicide and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:22

L136	4	(gate adj stack) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and plug and silicide and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:23
L137	4	(gate adj stack) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and plug and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:23
L138	17	(gate adj stack) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and contactless	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:27
L139	5	(gate adj stack) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and contactless and ((resist or photoresist or photo-resist) near2 (pattern or patterning or patterned))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 15:28
L140	10	(gate adj stack) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and contactless and ((resist or photoresist or photo-resist) near5 (pattern or patterning or patterned))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 16:14
L141	10	(gate adj stack) and (bl or bitline or bit-line or (bit near line)) and (nor near2 (type or cell or array or memory)) and (control near gate) and (etch or etching or etched) and contactless and ((resist or photoresist or photo-resist) near5 (pattern or patterning or patterned)) and (floating adj gate) and (control adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 16:35

L142	5	l141 and ((etch or etching) near2 (stop or barrier))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 16:35